



STB27NM60ND STW27NM60ND

N-channel 600 V, 0.13 Ω , 21 A FDmesh™ II Power MOSFET
(with fast diode) in D²PAK, TO-247

Features

Type	V _{DSS} @ T _{JMAX}	R _{DS(on)} max	I _D
STB27NM60ND	650 V	0.16 Ω	21 A
STW27NM60ND			21 A

- The worldwide best R_{DS(on)}*area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities

Application

- Switching applications
 - Automotive

Description

These FDmesh™ II Power MOSFETs with intrinsic fast-recovery body diode are produced using the second generation of MDmesh™ technology. Utilizing a new strip-layout vertical structure, these revolutionary devices feature extremely low on-resistance and superior switching performance. They are ideal for bridge topologies and ZVS phase-shift converters.

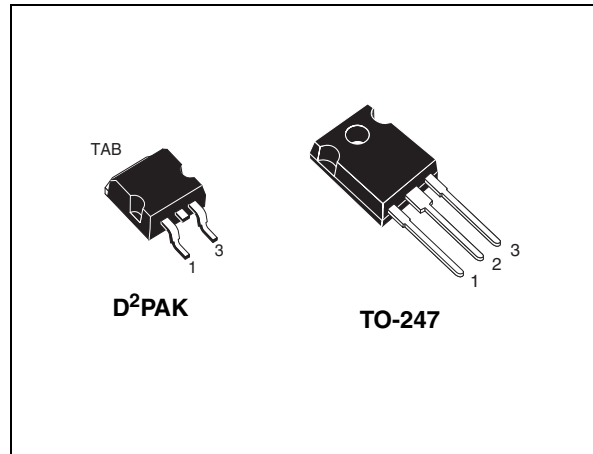


Figure 1. Internal schematic diagram

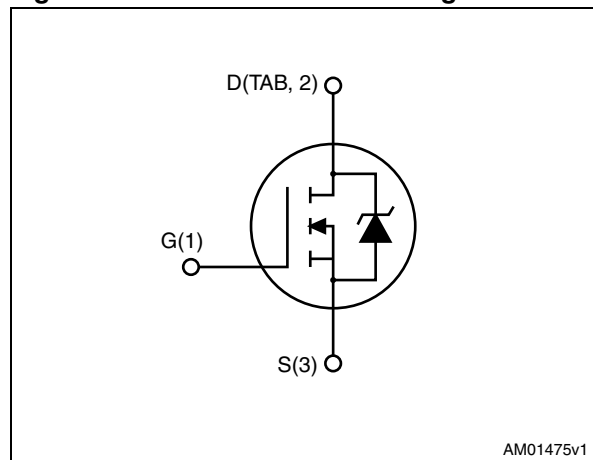


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB27NM60ND	27NM60ND	D ² PAK	Tape and reel
STW27NM60ND	27NM60ND	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	21	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	13	A
$I_{DM}^{(1)}$	Drain current (pulsed)	84	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	160	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	40	V/ns
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_J	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area
2. $I_{SD} \leq 21\text{ A}$, $di/dt \leq 600\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	D ² PAK	TO-247	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.78		$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max		50	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient max	30		$^\circ\text{C}/\text{W}$

1. When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max)	10	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$)	850	mJ

2 Electrical characteristics

($T_{CASE}=25\text{ °C}$ unless otherwise specified).

Table 5. On/off states

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain source voltage slope	$V_{DD} = 480\text{ V}$, $I_D = 21\text{ A}$, $V_{GS} = 10\text{ V}$	48			V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600\text{ V}$ $V_{DS} = 600\text{ V}$ @ $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 10.5\text{ A}$		0.13	0.16	Ω

1. Characteristic value at turn off on inductive load.

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$, $I_D = 10.5\text{ A}$	-	17	-	S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	2400 150 15	-	pF pF pF
$C_{oss\ eq.}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }480\text{ V}$	-	320	-	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 300\text{ V}$, $I_D = 10.5\text{ A}$ $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 21), (see Figure 16)	-	60 30 50 40	-	ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480\text{ V}$, $I_D = 21\text{ A}$, $V_{GS} = 10\text{ V}$, (see Figure 17)	-	80 15 40	-	nC nC nC
R_g	Gate input resistance	$f = 1\text{ MHz}$ gate DC bias = 0 Test signal level = 20 mV open drain	-	1.6	-	Ω

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		21	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		84	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 21\text{ A}, V_{GS} = 0$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ <i>(see Figure 18)</i>	-	160		ns
Q_{rr}	Reverse recovery charge			1		μC
I_{RRM}	Reverse recovery current			15		A
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 150\text{ }^\circ\text{C}$ <i>(see Figure 18)</i>	-	230		ns
Q_{rr}	Reverse recovery charge			2		μC
I_{RRM}	Reverse recovery current			19		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK

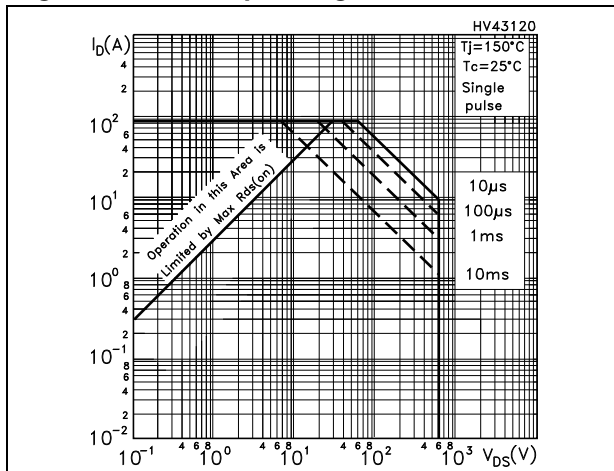


Figure 3. Thermal impedance for D²PAK

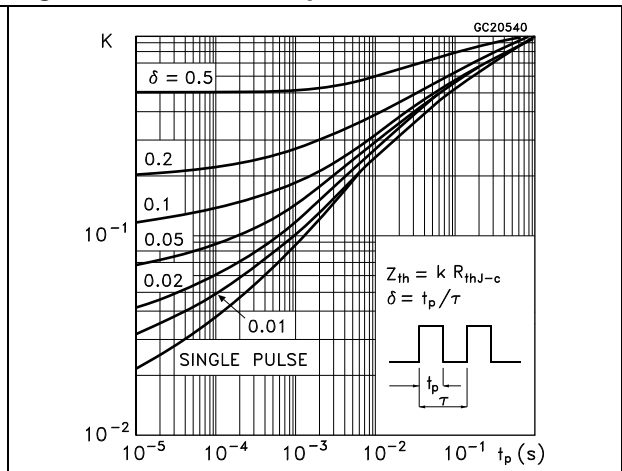


Figure 4. Safe operating area for TO-247

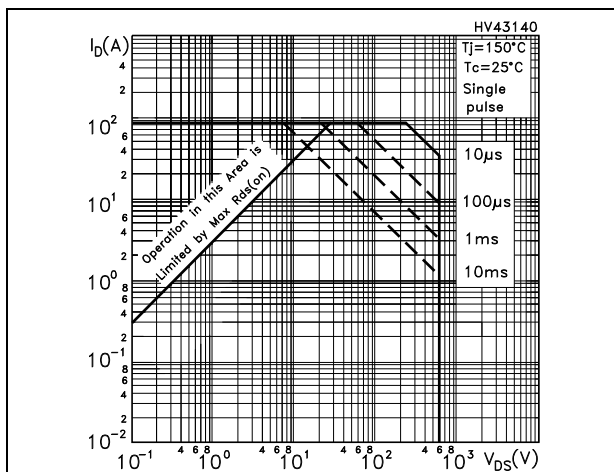


Figure 5. Thermal impedance for TO-247

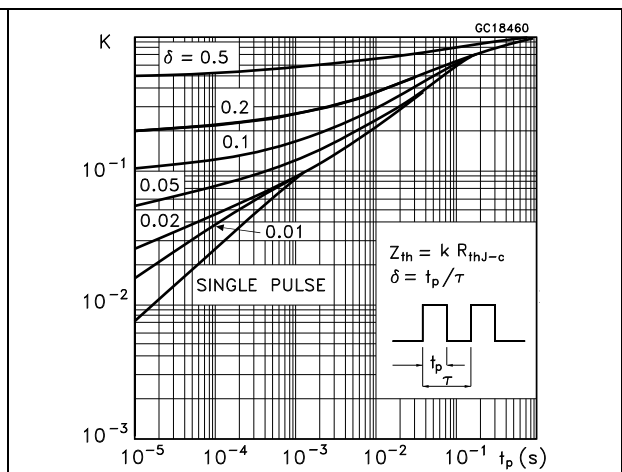


Figure 6. Output characteristics

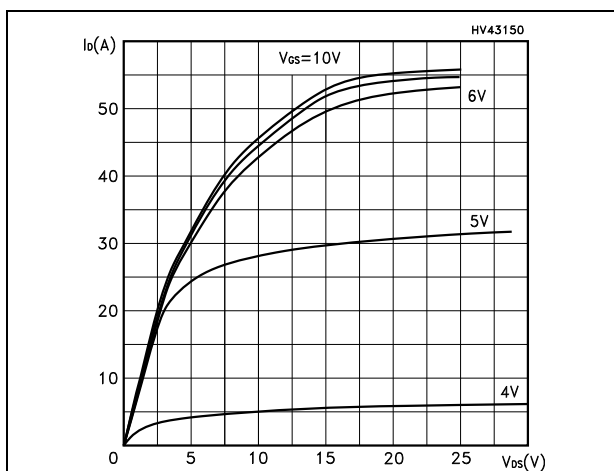


Figure 7. Transfer characteristics

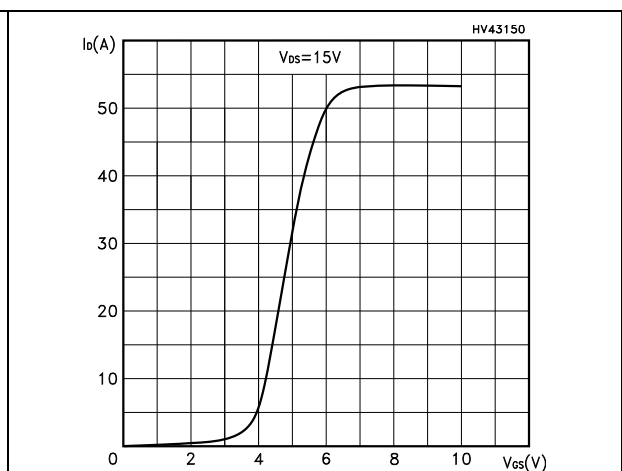


Figure 8. Transconductance

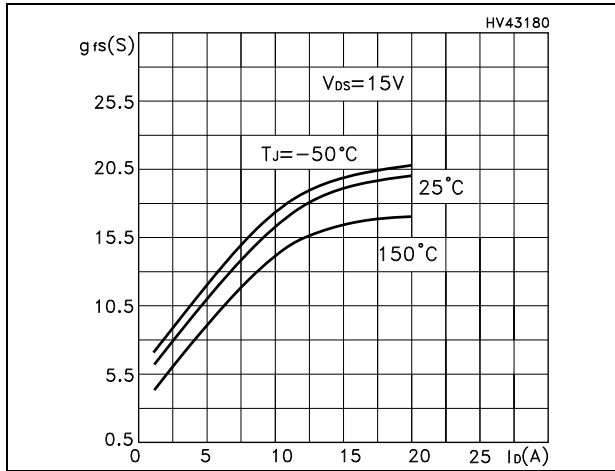


Figure 9. Static drain-source on resistance

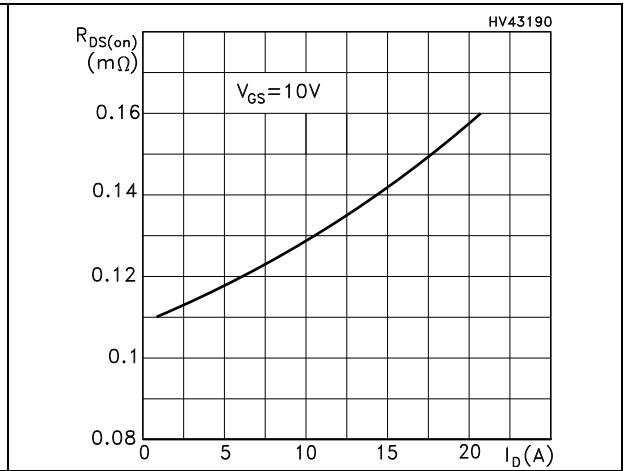


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

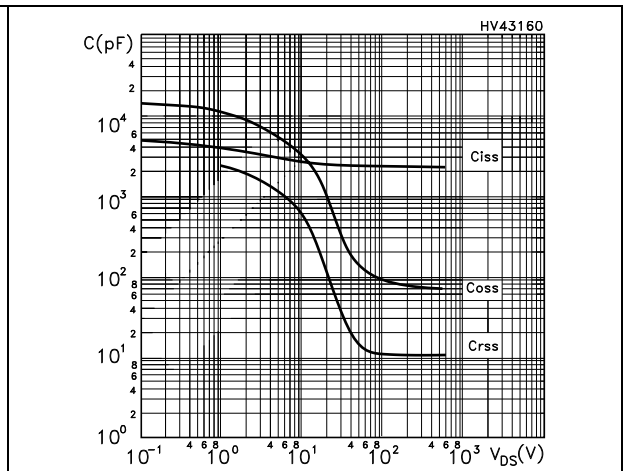
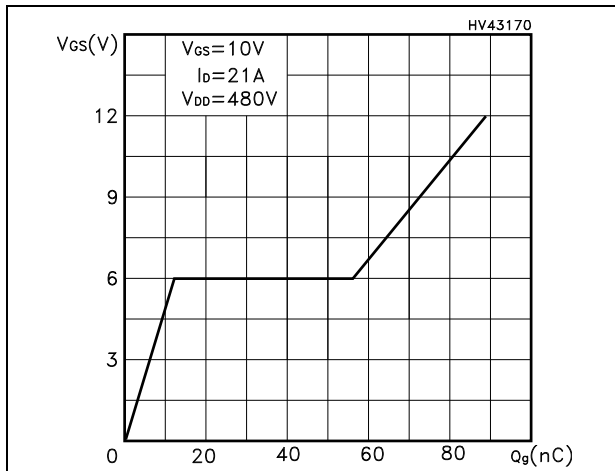


Figure 12. Normalized gate threshold voltage vs temperature

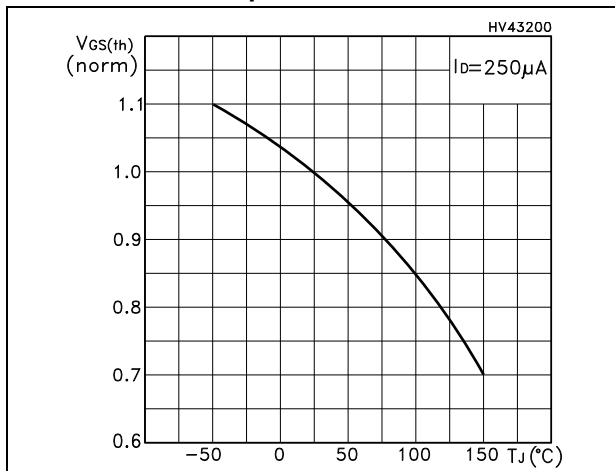


Figure 13. Normalized on resistance vs temperature

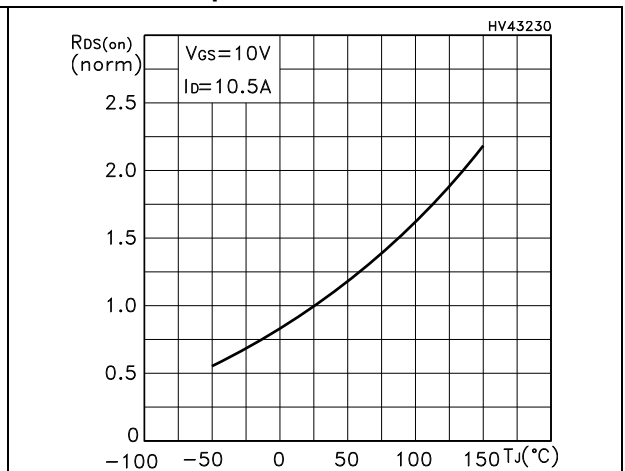


Figure 14. Source-drain diode forward characteristics

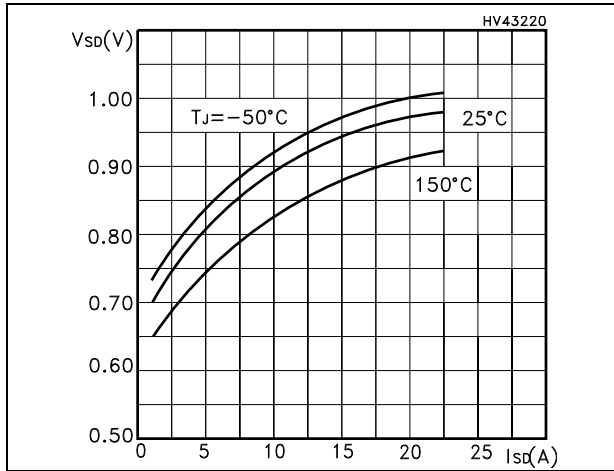
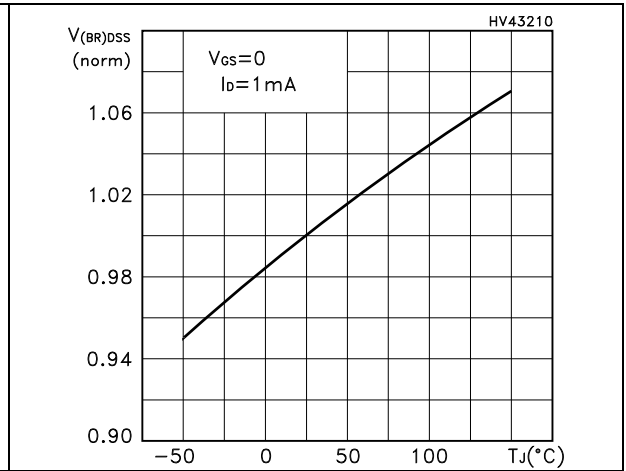


Figure 15. Normalized $B_{V_{DSS}}$ vs temperature



3 Test circuits

Figure 16. Switching times test circuit for resistive load

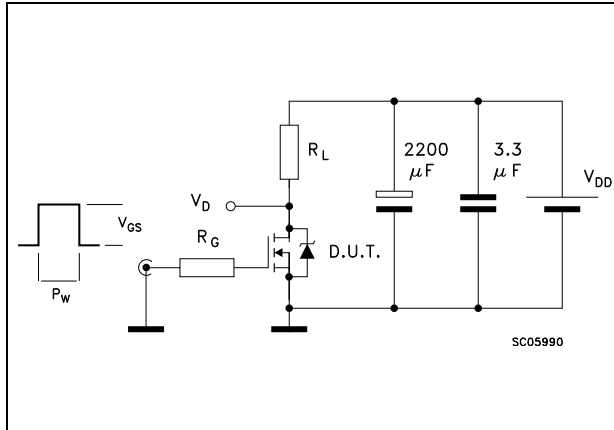


Figure 17. Gate charge test circuit

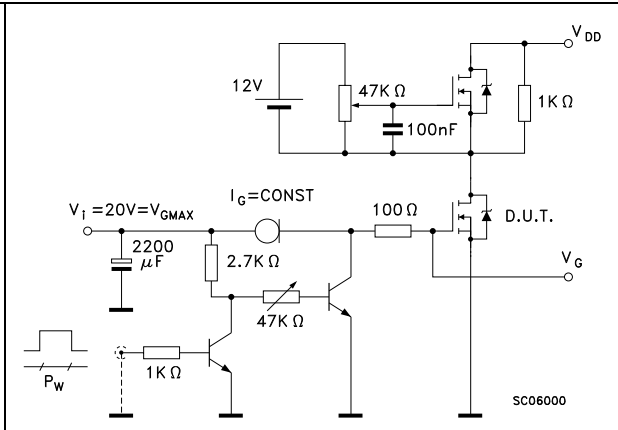


Figure 18. Test circuit for inductive load switching and diode recovery times

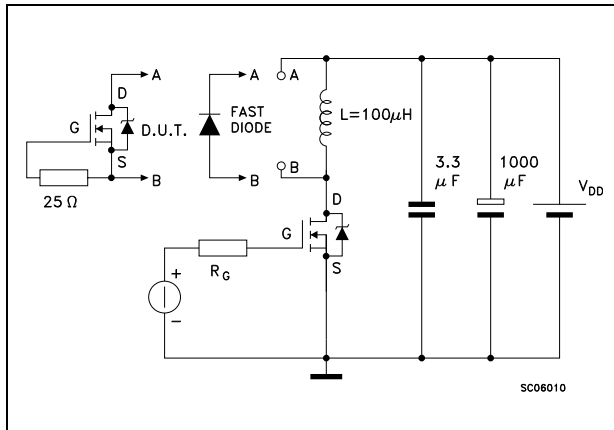


Figure 19. Unclamped inductive load test circuit

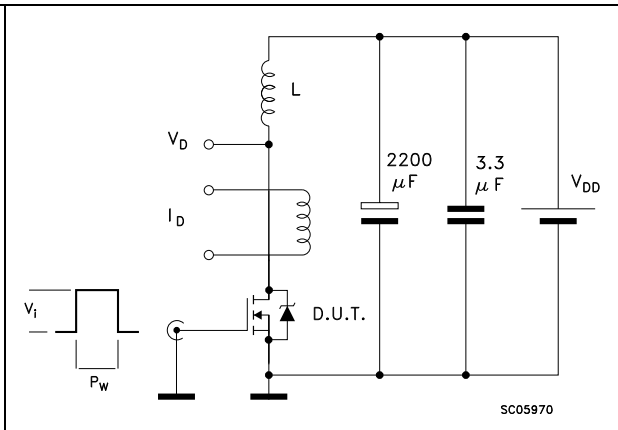


Figure 20. Unclamped inductive waveform

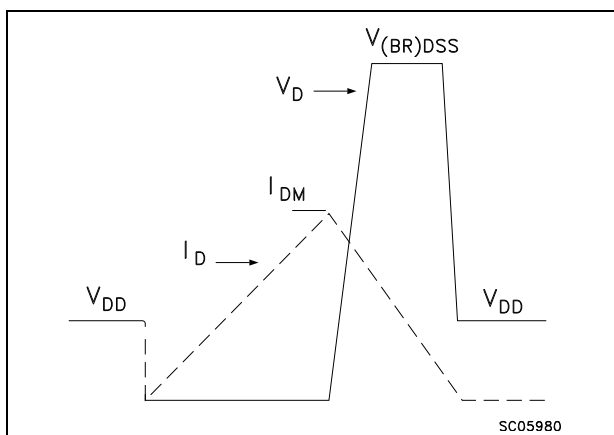
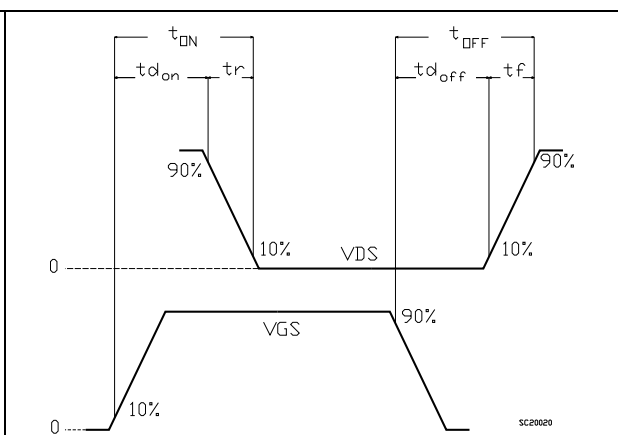


Figure 21. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22. D²PAK (TO-263) drawing

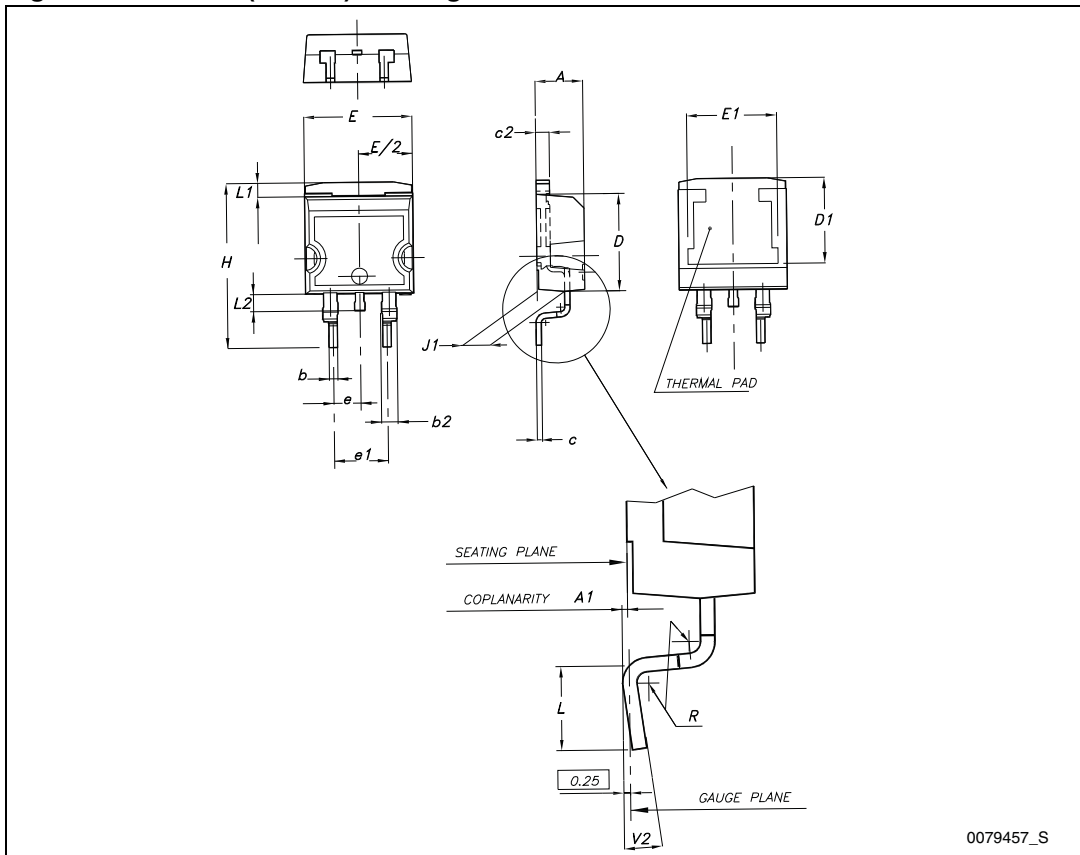
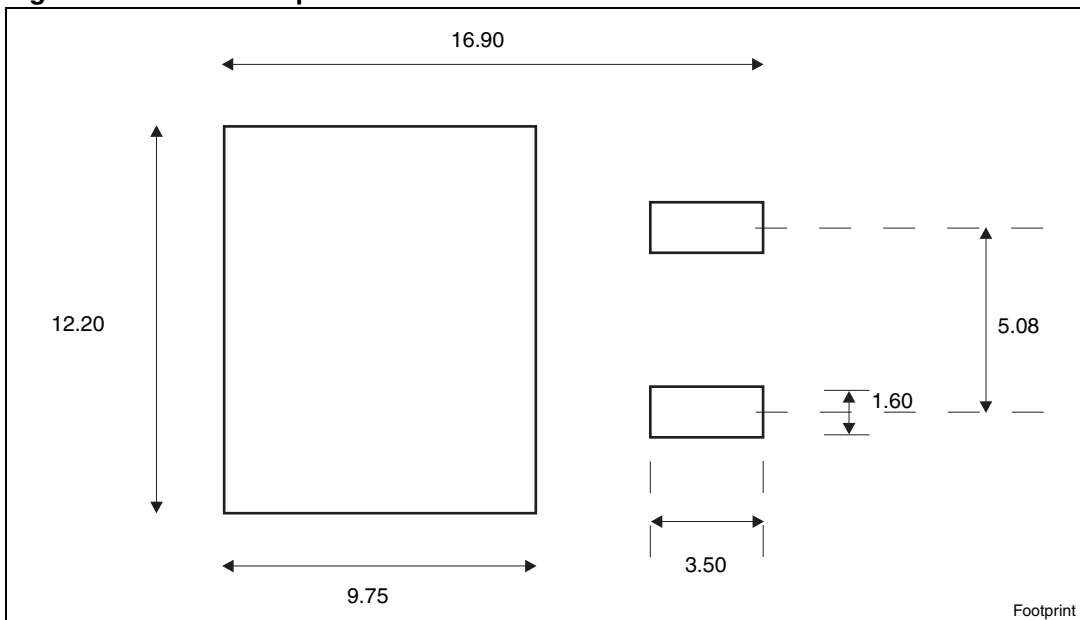


Figure 23. D²PAK footprint^(a)

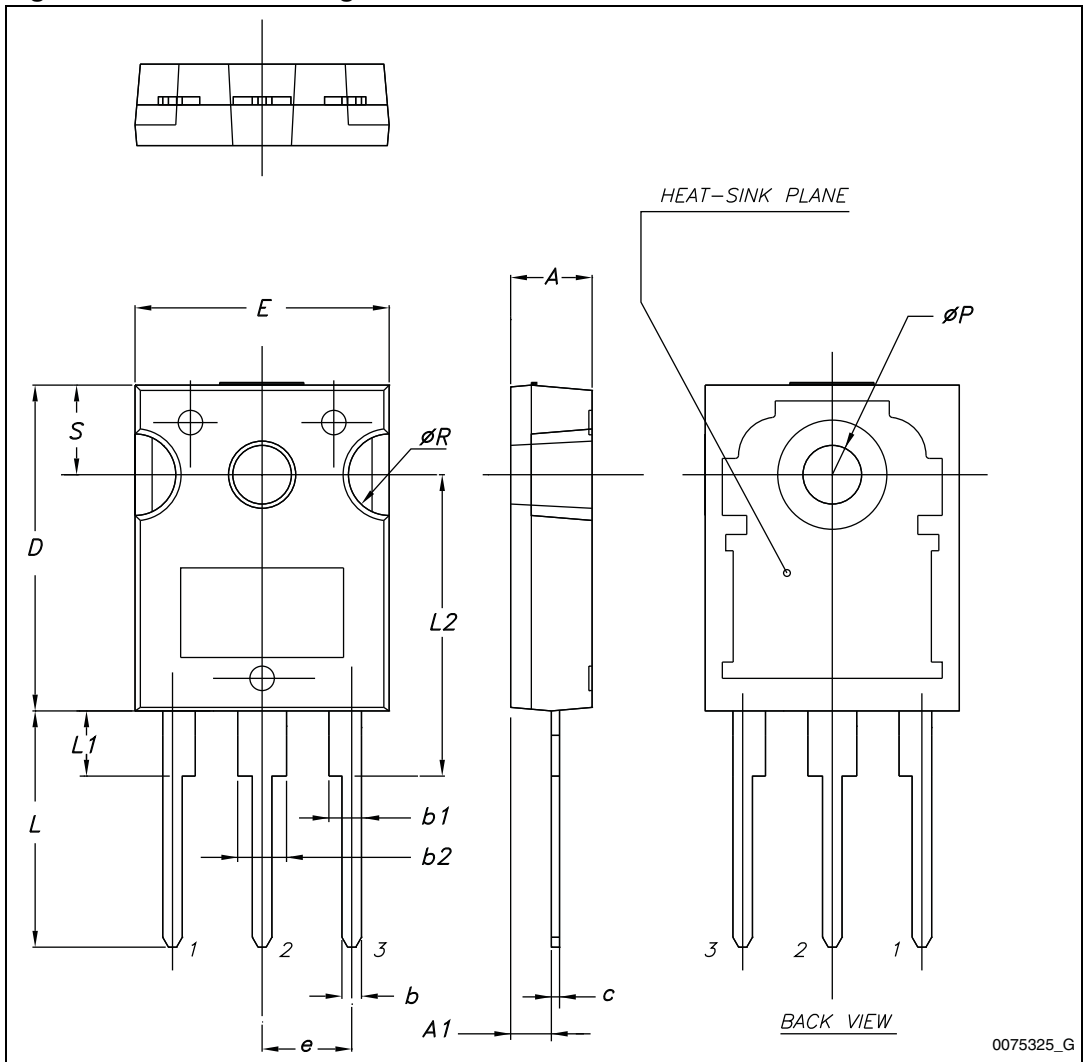


a. All dimension are in millimeters

Table 9. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 24. TO-247 drawing



5 Packing mechanical data

Table 10. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 25. Tape

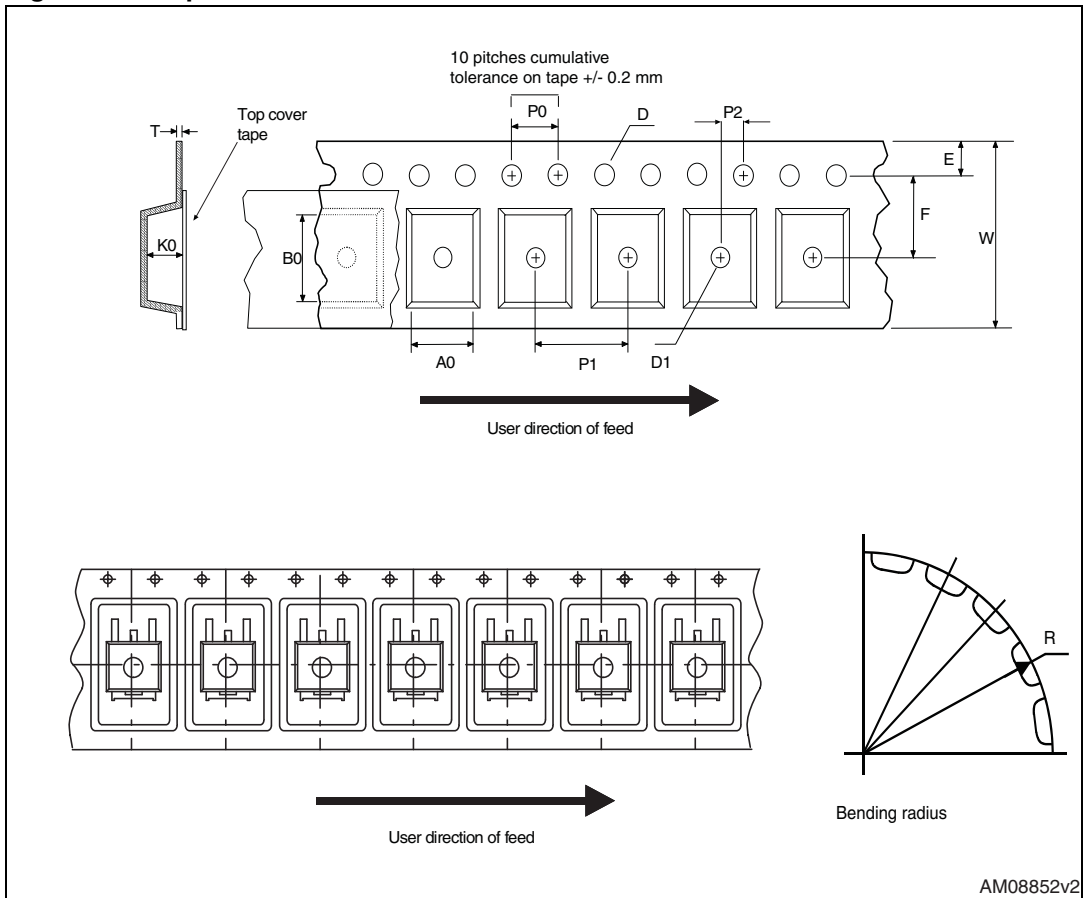
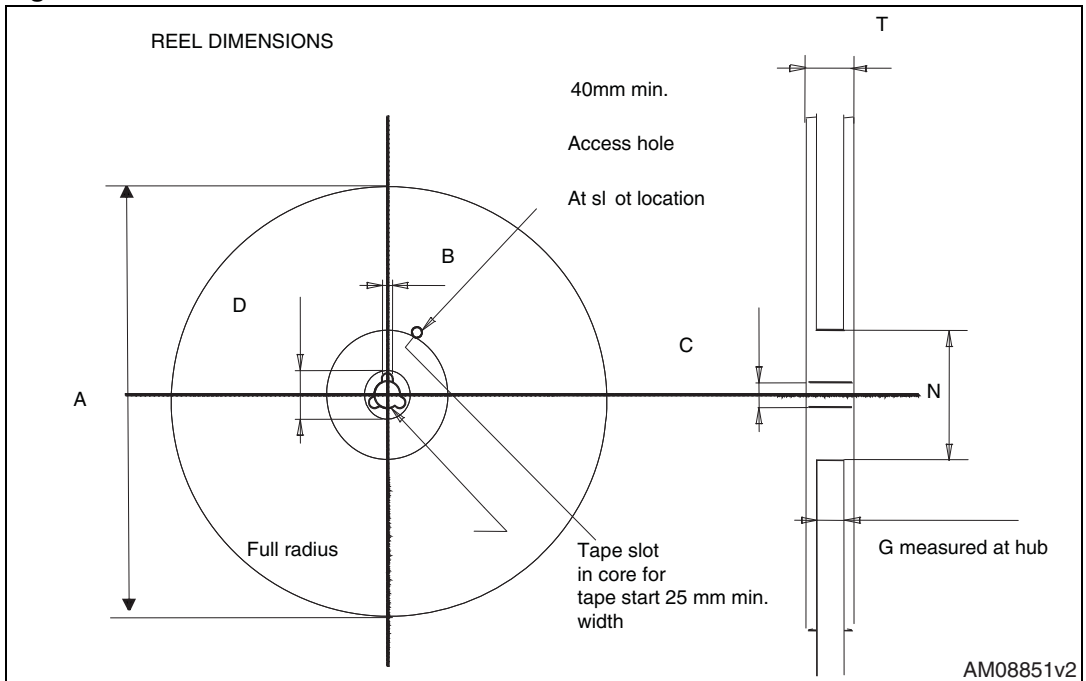


Figure 26. Reel



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
02-Mar-2009	1	First release.
08-Mar-2011	2	Document status promoted from preliminary data to datasheet.
28-Nov-2011	3	Inserted new device in D ² PAK. Updated Table 1: Device summary , Table 3: Thermal data , Section 3: Test circuits and Section 4: Package mechanical data Inserted Section 5: Packing mechanical data . – Minor text changes.

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